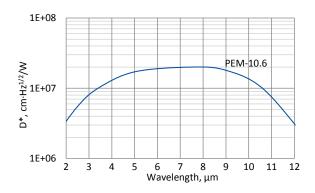


## 2.23 PEM series

# 2.23.1 2.0 – 12.0 μm HgCdTe ambient temperature photoelectromagnetic detectors

**PEM series** features uncooled HgCdTe photovoltaic IR detectors based on photelectromagnetic effect in the semiconductor – spatial separation of optically generated electrons and holes in the magnetic field. The devices are designed for the maximum performance at 10.6 μm and especially useful as a large active area detectors to detect CW and low frequency modulated radiation. These devices are mounted in specialized packages with incorporated magnetic circuit inside. 3° wedged zinc selenide anti-reflection coated (wZnSeAR) window prevents unwanted interference effects and protects against pollution.

## Spectral response (T<sub>a</sub> = 20°C)





Exemplary spectral detectivity, the spectral response of delivered devices may differ.

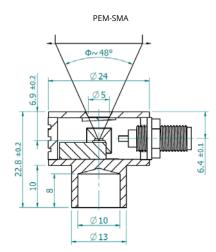
### Specification (T<sub>a</sub> = 20°C)

Parameter	Detector type	
	PEM-10.6	
Active element material	epitaxial HgCdTe heterostructure	
Optimum wavelength $\lambda_{\mathrm{opt'}}$ $\mu\mathrm{m}$	10.6	
Detectivity D*( $\lambda_{peak}$ ), cm·Hz <sup>1/2</sup> /W	≥2.0×10 <sup>7</sup>	
Detectivity D*( $\lambda_{opt}$ ), cm·Hz <sup>1/2</sup> /W	≥1.0×10 <sup>7</sup>	
Current responsivity-active area length product $R_{_{\rm I}}(\lambda_{_{\rm opt}})$ -L, A·mm/W	≥0.002	
Time constant $\tau$ , ns	≤1.2	
Resistance R, $\Omega$	≥40	
Active area A, mm×mm	1×1, 2×2	
Package	PEM-SMA	PEM-TO8
Acceptance angle Φ	~48°	~52°
Window	wZnSeAR	

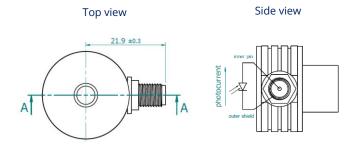
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# Mechanical layout, mm



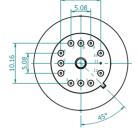
 $\boldsymbol{\Phi}$  – acceptance angle



# PEM-TO8 Dec 52° Dec

Φ – acceptance angle

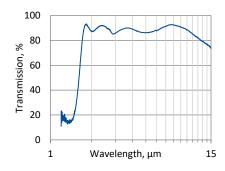
# Bottom view





Function	Pin number
Detector	1, 3
Chassis ground	11
Not used	2, 4, 5, 6, 7, 8, 9, 10, 12

## Spectral transmission of wZnSeAR window (typical example)



# **Dedicated preamplifier**



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